Fundamental description of (field induced) Josephson junctions coupling with semiconductor position based electrostatic qubits

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First Section

- Essence of Josephson junction
- Andreev Bound State

2 Field induced Josephson junction

- Osition based semiconductor devices
- Interface between semiconductor qubit and Josephson junction

Essence of Josephson effct



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Josephson Junction



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JJs vs semiconductor qubits

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Concept of position based semiconductor qubit



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The Hamiltonian of this system is given as

$$\hat{H}(t) = \begin{pmatrix} E_{p1}(t) & t_{s12}(t) \\ t_{s12}^{\dagger}(t) & E_{p2}(t) \end{pmatrix}_{[x=(x_1,x_2)]} = (E_1(t) |E_1\rangle_t \langle E_1|_t + E_2(t) |E_2\rangle \langle E_2|)_{[E=(x_1,x_2)]}$$
(1)
The Hamiltonian $\hat{H}(t)$ eigenenergies $E_1(t)$ and $E_2(t)$ with $E_2(t) > E_1(t)$

are given as

$$E_{1}(t) = \left(-\sqrt{\frac{(E_{\rho1}(t) - E_{\rho2})^{2}}{4} + |t_{s12}(t)|^{2}} + \frac{E_{\rho1}(t) + E_{\rho2}(t)}{2}\right),$$

$$E_{2}(t) = \left(+\sqrt{\frac{(E_{\rho1}(t) - E_{\rho2})^{2}}{4} + |t_{s12}(t)|^{2}} + \frac{E_{\rho1}(t) + E_{\rho2}(t)}{2}\right), \quad (2)$$

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Having Hermitian matrix \hat{A} with real valued coefficients $a_{11}(t)$, $a_{22}(t)$, $a_{12r}(t)$, $a_{12i}(t)$ we observe that

$$\hat{A}_{2\times 2} = \begin{pmatrix} a_{11} & a_{12r} + ia_{12i} \\ a_{12r} - ia_{12i} & a_{22} \end{pmatrix},$$
(3)

$$\exp(\frac{1}{\hbar i}\hat{A}_{2\times 2}) = \begin{pmatrix} e^{\frac{1}{\hbar}(a_{11})} & e^{(\frac{1}{\hbar}a_{12r} + ia_{12i})} \\ e^{\frac{1}{\hbar}(a_{12r} - ia_{12i})} & e^{\frac{1}{\hbar}(a_{22})} \end{pmatrix}$$
(4)

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For $\hat{A}_{N \times N}$ we obtain

$$\exp(\frac{1}{\hbar i}\hat{A}_{N\times N}) = \begin{pmatrix} e^{\frac{1}{\hbar}(a_{11})} & e^{(\frac{1}{\hbar}a_{12r}+ia_{12i})} & \dots & e^{(\frac{1}{\hbar}a_{1Nr}+ia_{1Ni})} \\ e^{\frac{1}{\hbar}(a_{12r}-ia_{12i})} & e^{\frac{1}{\hbar}(a_{22})} & \dots & e^{(\frac{1}{\hbar}a_{2Nr}+ia_{2Ni})} \\ \dots & \dots & \dots & \dots \\ e^{(\frac{1}{\hbar}a_{N1r}-ia_{N1i})} & e^{(\frac{1}{\hbar}a_{N2r}-ia_{N2i})} & \dots & e^{(\frac{1}{\hbar}a_{N,N})} \end{pmatrix}$$
(5)

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Using the above property for matrix of size 2 by 2 we obtain

$$\begin{pmatrix}
e^{\frac{1}{i\hbar}\int_{t_{0}}^{t}\hat{H}(t_{1})dt_{1}} = \hat{U}(t, t_{0}) = \\
e^{\frac{1}{i\hbar}(\int_{t_{0}}^{t}E_{p1}(t_{1})dt_{1})} & e^{\frac{1}{i\hbar}(\int_{t_{0}}^{t}t_{sr}(t_{1})dt_{1}+i\int_{t_{0}}^{t}t_{si}(t_{1})dt_{1})} \\
e^{\frac{1}{i\hbar}(\int_{t_{0}}^{t}t_{sr}(t_{1})dt_{1}-i\int_{t_{0}}^{t}t_{si}(t_{1})dt_{1})} & e^{\frac{1}{i\hbar}(\int_{t_{0}}^{t}E_{p2}(t_{1})dt_{1})}
\end{pmatrix}$$
(6)



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Concept of programmable quantum matter



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The state of Josephson junction is well described by Bogoliubov-de Gennes equation

$$\begin{pmatrix} H_0 & \Delta(x) \\ \Delta(x) & -H_0^{\dagger} \end{pmatrix} \begin{pmatrix} u_n(x) \\ v_n(x) \end{pmatrix} = E_n \begin{pmatrix} u_n(x) \\ v_n(x) \end{pmatrix}.$$
 (7)

Semiconductor single electron line with 2 nodes can be regarded as electrostatic position dependent qubit and can be described by

$$H_{semi} = ts_{1,2}|1> < 2| + ts_{2,1}|2> < 1| + E_{p1}|1> < 1| + E_{p2}|2> < 2|,$$

We can express coupling of 2 systems assuming 4 nodes for electron or hole and 2 nodes for electron confined in semiconductor so we have eigenvector having 16 components $|0_{Ee} > |Es_1 >, |0_{Ee} > |Es_2 >, |1_{Ee} > |Es_1 >, |1_{Ee} > |Es_2 >, ..., |3_{Ee} > |Es_1 >, |3_{Ee} > |Es_2 >, |0_{Eh} > |Es_1 >, |0_{Ee} > |Es_2 >, ..., |3_{Eh} > |Es_1 >, |3_{Eh} > |Es_2 >.$

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Interace betweem semiconductor qubit and Josephson junction



Josephson junction

electrostatic semiconductor qubit

Interaction Hamiltonian between semiconductor qubit and Josephson junction

/ Ep + mu +	V ts	tt	0	0	0	0	0	Delta	0	0	0	0	0	0	0 \
ts	Ep + mu + V	0	tt	0	0	0	0	0	Delta	0	0	0	0	0	0
tt	0	$Ep + \frac{g^2}{a} + V$	ts	tt	0	0	0	0	0	0	0	0	0	0	0
0	tt	ts	$Ep + \frac{q^2}{b} + V$	0	tt	0	0	0	0	0	0	0	0	0	0
0	0	tt	0	$Ep+\frac{q^2}{b}+V$	ts	tt	0	0	0	0	0	0	9	0	0
0	0	0	tt	ts	$Ep + \frac{q^2}{2} + V$	0	tt	0	0	0	0	0	0	0	0
0	9	0	0	tt	ø	Ep + mu + V	ts	0	0	0	0	0	0	Delta	0
0	0	0	0	0	tt	ts	Ep + mu + V	0	0	0	0	0	0	0	Delta
Delta	0	0	0	0	0	0	0	Ep - mu - V	ts	-tt	0	0	0	0	0
0	Delta	0	0	0	0	0	0	ts	Ep - mu - V	0	-tt	0	0	0	0
0	0	0	0	0	0	0	0	-tt	0	$Ep=\frac{q^2}{a}=V$	ts	-tt	0	0	0
0	0	0	0	0	0	0	0	0	-tt	ts	$Ep = \frac{g^2}{b} = V$	0	-tt	0	0
0	0	0	0	0	0	0	0	0	0	-tt	0	Ep - <u>a²</u> - V	ts	-tt	0
0	0	0	0	0	0	0	0	0	0	0	-tt	ts	Ep - 92 - V	0	-tt
0	0	0	0	0	9	Delta	0	0	0	0	0	-tt	0	Ep - mu - V	ts
0	0	0	0	0	0	0	Delta	0	0	0	0	0	-tt	ts	Ep - mu - V

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{Eigenenergies of Josephson junction coupled to SELs(|∆|=1)} Energy

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JJs vs semiconductor qubits

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Figure: Eigenenergy spectral of semiconductor qubit coupled to Josephson junction obtained from simplistic tight-binding model (tight-binding BdGe coupled to tight-binding Schroedinger equation for semiconductor qubit).

Further extensions of tight-binding model



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- Quantum phase transition is expected to occur both in electrostatically coupled semiconductor qubits and systems of coupled Josephson junction to superconducting qubit.
- Increase of superconducting order parameter has similar impact on energy eigenspectrum as the increase of distance between superonducting Josephson junction and semiconductor qubit.

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